

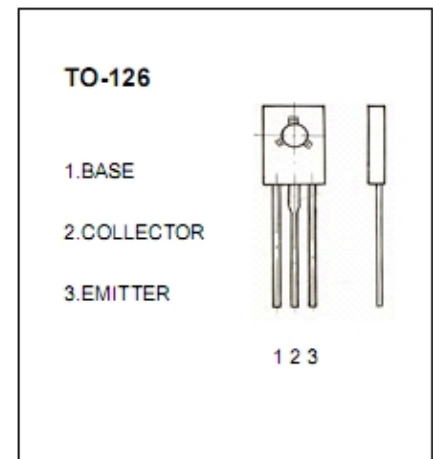
TO-126 Plastic-Encapsulate Transistors

ALJ13003

TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

MAXI	Parameter	Value	Units
VCBO	Collector-Base Voltage	600	V
VCEO	Collector-Emitter Voltage	400	V
VEBO	Emitter-Base Voltage	9	V
IC	Collector Current	1.5	A
PC	Collector Power Dissipation	50	W
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =100μA, I _E =0	600			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C =1mA, I _B =0	400			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _C =100μA, I _C =0	9			V
Collector cut-off current	I _{CBO}	V _{CB} =600V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =9V, I _C =0			0.1	μA
DC current gain	H _{FE}	V _{ce} =5V, I _c =200mA	15		30	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1.0A, I _B =0.25A			0.9	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =1.0A, I _B =0.25A			1.2	V
Storage Time	t _s	UI9600 I _C =0.25A	2.0		6.0	us
Rising Time	t _r				1	us
Fall Time	t _f				1	us
Transition Frequency	f _T	V _{CE} =10V, I _C =0.1A, f=1MHZ	5			MHZ